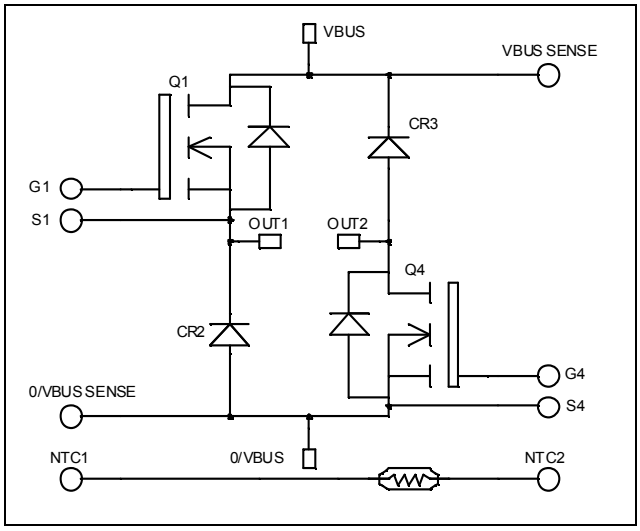
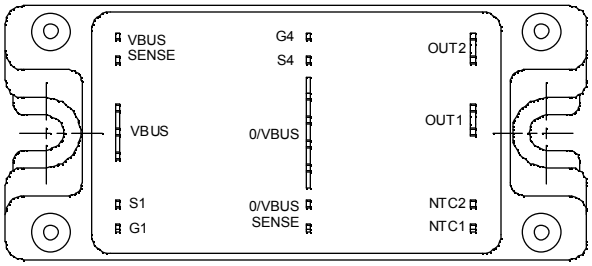
Asymmetrical - Bridge MOSFET Power Module

V_{DSS} = 200V
R_{DSon} = 20mΩ typ @ Tj = 25°C
I_D = 89A @ Tc = 25°C





Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Power MOS 7® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		200	V
I_D	Continuous Drain Current	T_c = 25°C	89	A
		T_c = 80°C	66	
I_{DM}	Pulsed Drain current		356	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		24	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	357	W
I_{AR}	Avalanche current (repetitive and non repetitive)		89	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 200V	T_j = 25°C			100	µA
		V_{GS} = 0V, V_{DS} = 160V	T_j = 125°C			500	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 44.5A			20	24	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 2.5mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±100	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		6850		pF
C_{oss}	Output Capacitance			2180		
C_{rss}	Reverse Transfer Capacitance			97		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 100V I_D = 75A		112		nC
Q_{gs}	Gate – Source Charge			43		
Q_{gd}	Gate – Drain Charge			47		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 133V I_D = 75A R_G = 5Ω		28		ns
T_r	Rise Time			56		
$T_{d(off)}$	Turn-off Delay Time			81		
T_f	Fall Time			99		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 133V I_D = 75A, R_G = 5Ω		463		µJ
E_{off}	Turn-off Switching Energy			455		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 133V I_D = 75A, R_G = 5Ω		608		µJ
E_{off}	Turn-off Switching Energy			531		

Diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=200V	T_j = 25°C			250	µA
			T_j = 125°C			500	
I_F	DC Forward Current		T_c = 80°C		100		A
V_F	Diode Forward Voltage	I_F = 100A			1	1.1	V
		I_F = 200A			1.4		
		I_F = 100A	T_j = 125°C		0.9		
t_{rr}	Reverse Recovery Time	I_F = 100A V_R = 133V di/dt = 200A/µs	T_j = 25°C		60		ns
			T_j = 125°C		110		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		200		nC
			T_j = 125°C		840		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		Transistor			0.35	°C/W
			Diode			0.55	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

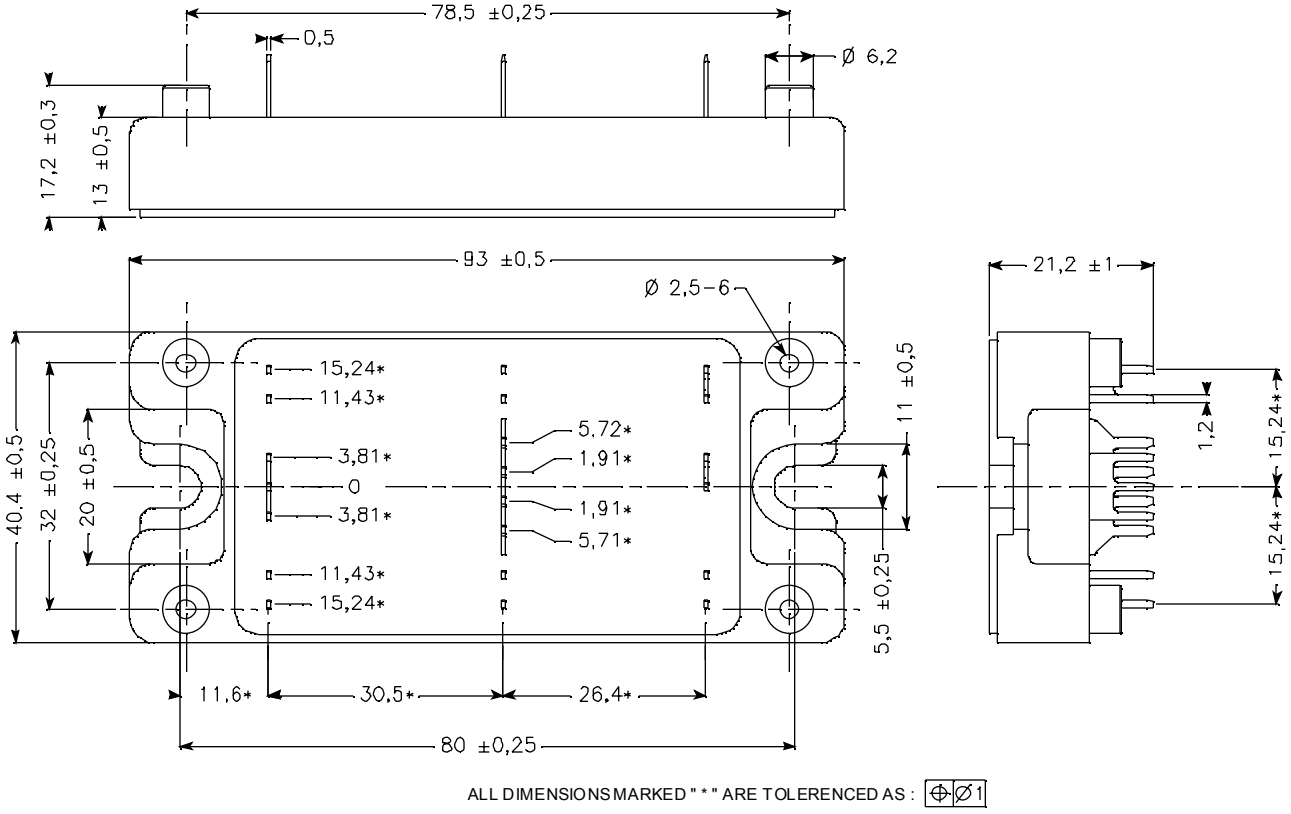
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		kΩ
$B_{25/85}$	T_{25} = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

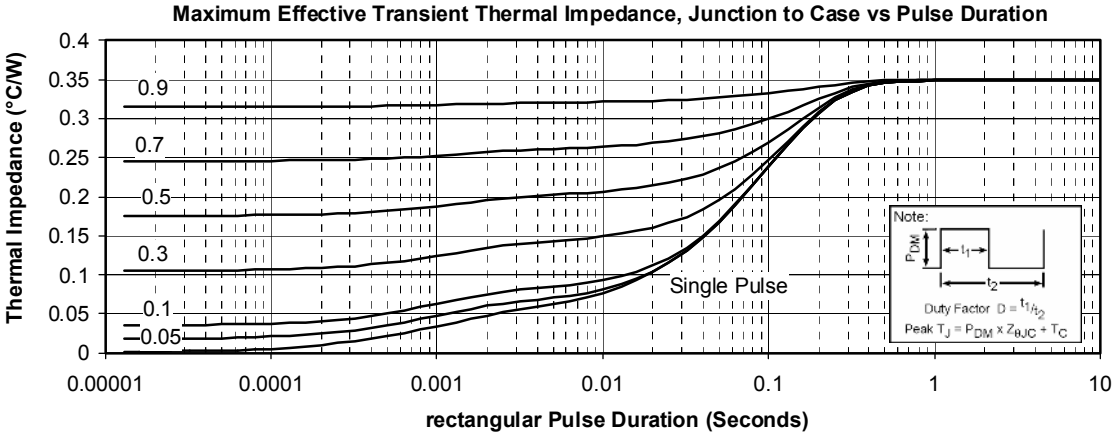
SP4 Package outline (dimensions in mm)

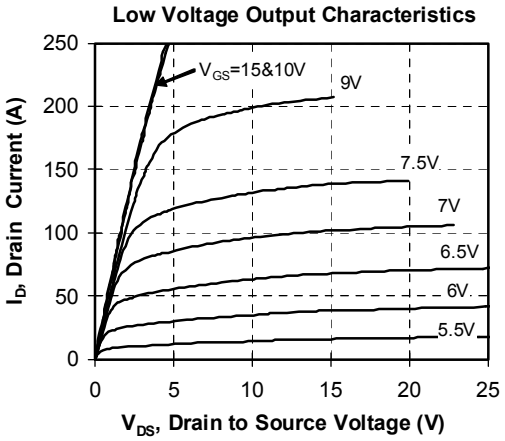


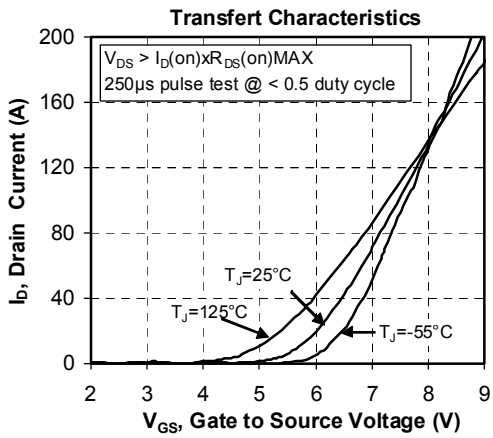
ALL DIMENSIONS MARKED " * " ARE TOLERENCED AS : ⊕ Ø1

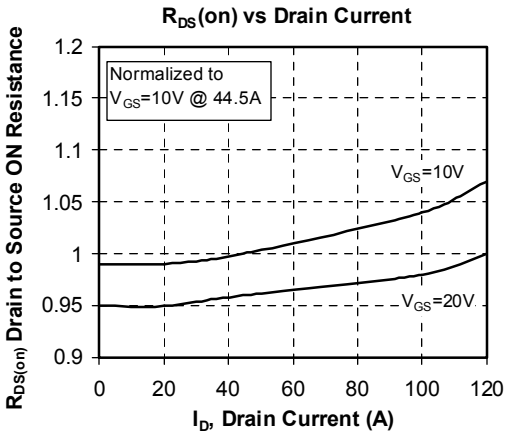
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

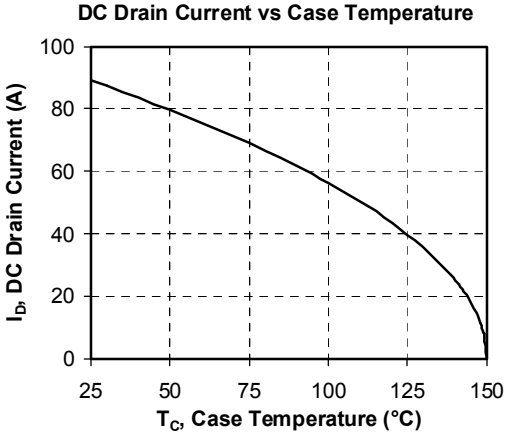
Typical Performance Curve



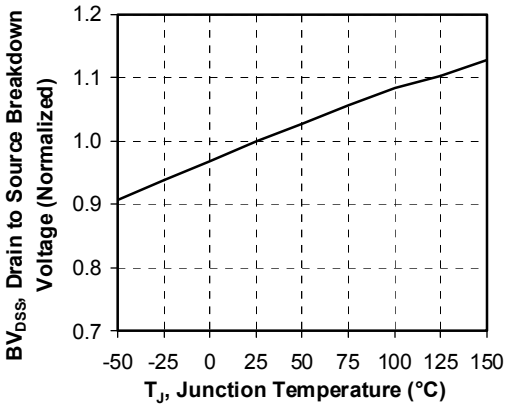




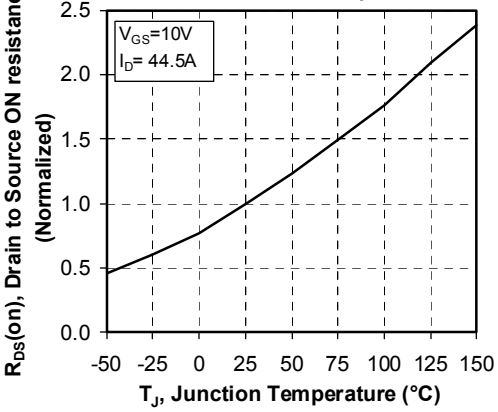




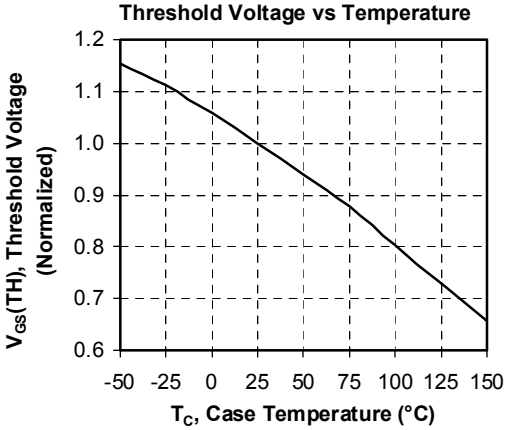
Breakdown Voltage vs Temperature



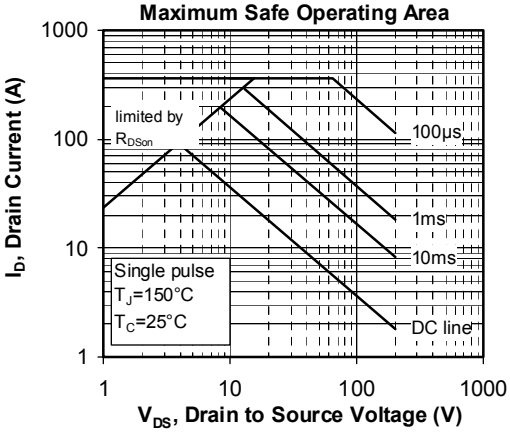
ON resistance vs Temperature



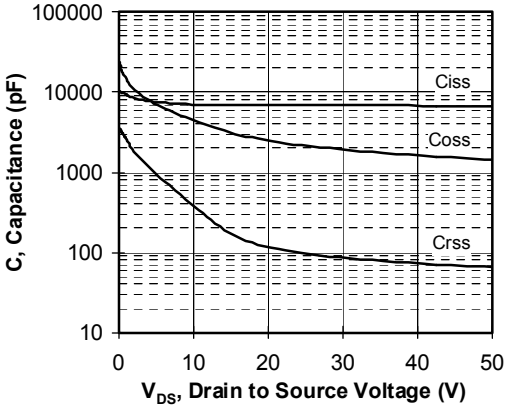
Threshold Voltage vs Temperature



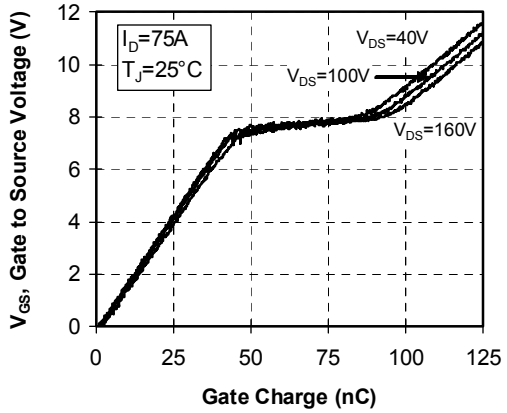
Maximum Safe Operating Area



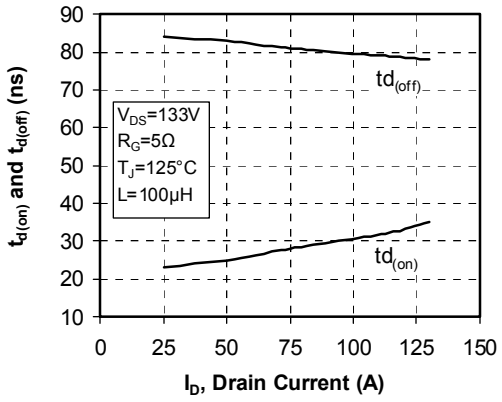
Capacitance vs Drain to Source Voltage



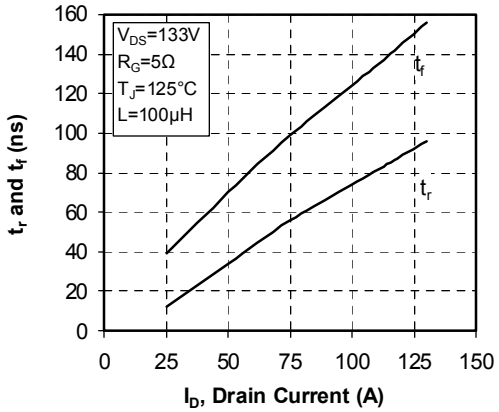
Gate Charge vs Gate to Source Voltage



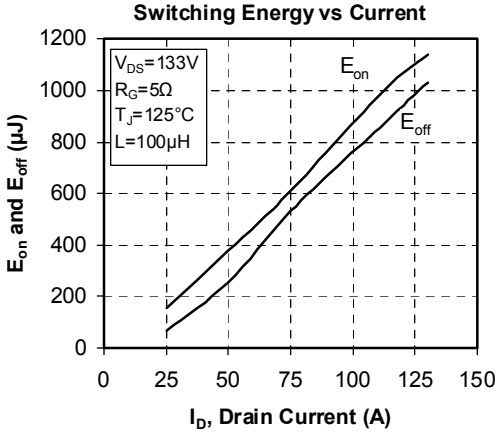
Delay Times vs Current



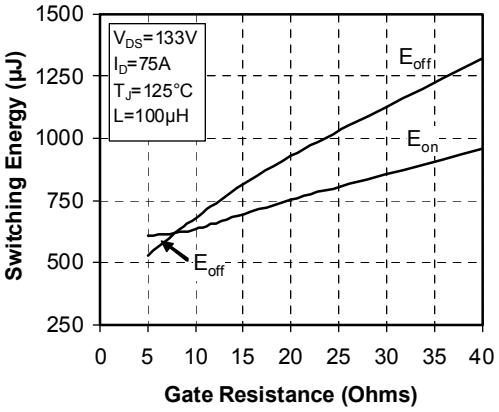
Rise and Fall times vs Current



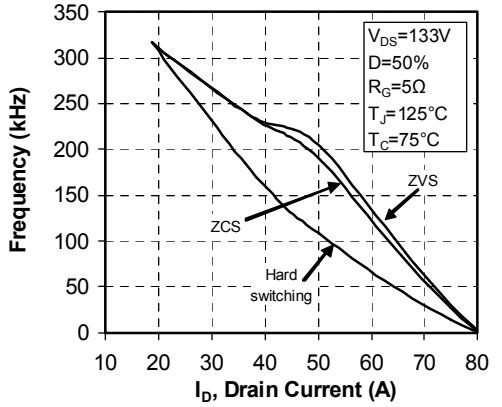
Switching Energy vs Current



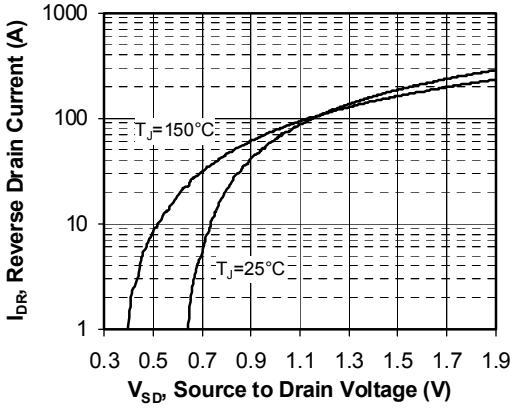
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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